PATENT ABSTRACTS OF JAPAN

(11)Publication number:

05-136417

(43)Date of publication of application: 01.06.1993

(51)Int.CI.

H01L 29/784 H01L 27/12

(21)Application number: 04-108039

(22)Date of filing:

27.04.1992

(71)Applicant : SEIKO EPSON CORP

(72)Inventor: OSHIMA HIROYUKI

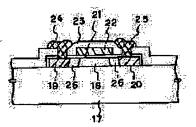
(54) SEMICONDUCTOR DEVICE

(57)Abstract:

PURPOSE: To reduce leakage current in an OFF state of a thin

film transistor.

CONSTITUTION: In a semiconductor device having a thin film transistor formed on a substrate, a semiconductor device where the thin film transistor consists of a thin polycrystalline film semiconductor 18 and has a low-doped region 26 adjacent to at_ least either the source region 19 or the drain region 20 of the thin film transistor and equal to this region in conductivity.



LEGAL STATUS

[Date of request for examination]

27.04.1992

[Date of sending the examiner's decision of rejection] 23.05.1995

[Kind of final disposal of application other than the examiner's decision of rejection or application

converted registration]

[Date of final disposal for application]

[Patent number]

2525707

[Date of registration]

31.05.1996

[Number of appeal against examiner's decision of

07-13125

rejection]

[Date of requesting appeal against examiner's decision 22.06.1995

of rejection]

[Date of extinction of right]

Copyright (C); 1998,2000 Japan Patent Office